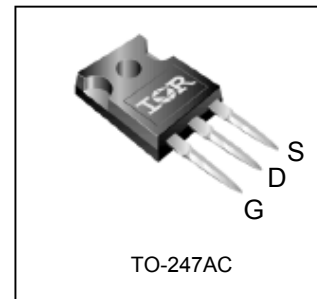
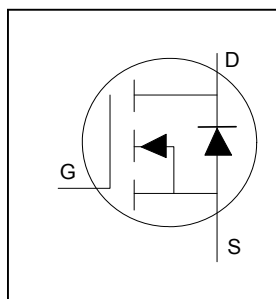


|                          |                                |
|--------------------------|--------------------------------|
| $V_{DS}$                 | <b>60V</b>                     |
| $R_{DS(on)}$ <b>typ.</b> | <b>2.1m<math>\Omega</math></b> |
| <b>max.</b>              | <b>2.5m<math>\Omega</math></b> |
| $I_D$ (Silicon Limited)  | <b>270A<sup>①</sup></b>        |
| $I_D$ (Package Limited)  | <b>195A</b>                    |



|          |          |          |
|----------|----------|----------|
| <b>G</b> | <b>D</b> | <b>S</b> |
| Gate     | Drain    | Source   |

### Applications

- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

### Benefits

- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free

| Base Part Number | Package Type | Standard Pack |          | Orderable Part Number |
|------------------|--------------|---------------|----------|-----------------------|
|                  |              | Form          | Quantity |                       |
| IRFP3006PbF      | TO-247       | Tube          | 25       | IRFP3006PbF           |

### Absolute Maximum Ratings

| Symbol                            | Parameter                                                    | Max.              | Units               |
|-----------------------------------|--------------------------------------------------------------|-------------------|---------------------|
| $I_D$ @ $T_C = 25^\circ\text{C}$  | Continuous Drain Current, $V_{GS}$ @ 10V (Silicon Limited)   | 270 <sup>①</sup>  | A                   |
| $I_D$ @ $T_C = 100^\circ\text{C}$ | Continuous Drain Current, $V_{GS}$ @ 10V (Silicon Limited)   | 190 <sup>①</sup>  |                     |
| $I_D$ @ $T_C = 25^\circ\text{C}$  | Continuous Drain Current, $V_{GS}$ @ 10V (Wire Bond Limited) | 195               |                     |
| $I_{DM}$                          | Pulsed Drain Current <sup>②</sup>                            | 1080              |                     |
| $P_D$ @ $T_C = 25^\circ\text{C}$  | Maximum Power Dissipation                                    | 375               | W                   |
|                                   | Linear Derating Factor                                       | 2.5               | W/ $^\circ\text{C}$ |
| $V_{GS}$                          | Gate-to-Source Voltage                                       | $\pm 20$          | V                   |
| dv/dt                             | Peak Diode Recovery <sup>④</sup>                             | 10                | V/ns                |
| $T_J$                             | Operating Junction and                                       | -55 to + 175      | $^\circ\text{C}$    |
| $T_{STG}$                         | Storage Temperature Range                                    |                   |                     |
|                                   | Soldering Temperature, for 10 seconds (1.6mm from case)      | 300               |                     |
|                                   | Mounting torque, 6-32 or M3 screw                            | 10lbf.in (1.1N.m) |                     |

### Avalanche Characteristics

|                              |                                            |                           |    |
|------------------------------|--------------------------------------------|---------------------------|----|
| $E_{AS}$ (Thermally limited) | Single Pulse Avalanche Energy <sup>③</sup> | 320                       | mJ |
| $I_{AR}$                     | Avalanche Current <sup>②</sup>             | See Fig. 14, 15, 22a, 22b | A  |
| $E_{AR}$                     | Repetitive Avalanche Energy <sup>⑤</sup>   |                           | mJ |

### Thermal Resistance

| Symbol          | Parameter                          | Typ. | Max. | Units                     |
|-----------------|------------------------------------|------|------|---------------------------|
| $R_{\theta JC}$ | Junction-to-Case <sup>⑧</sup>      | —    | 0.4  | $^\circ\text{C}/\text{W}$ |
| $R_{\theta CS}$ | Case-to-Sink, Flat Greased Surface | 0.24 | —    |                           |
| $R_{\theta JA}$ | Junction-to-Ambient                | —    | 40   |                           |

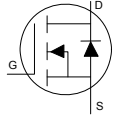
**Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

| Symbol                          | Parameter                            | Min. | Typ. | Max. | Units               | Conditions                                           |
|---------------------------------|--------------------------------------|------|------|------|---------------------|------------------------------------------------------|
| $V_{(BR)DSS}$                   | Drain-to-Source Breakdown Voltage    | 60   | —    | —    | V                   | $V_{GS} = 0V, I_D = 250\mu A$                        |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient  | —    | 0.07 | —    | V/ $^\circ\text{C}$ | Reference to $25^\circ\text{C}$ , $I_D = 5mA$ ②      |
| $R_{DS(on)}$                    | Static Drain-to-Source On-Resistance | —    | 2.1  | 2.5  | m $\Omega$          | $V_{GS} = 10V, I_D = 170A$ ⑤                         |
| $V_{GS(th)}$                    | Gate Threshold Voltage               | 2.0  | —    | 4.0  | V                   | $V_{DS} = V_{GS}, I_D = 250\mu A$                    |
| $I_{DSS}$                       | Drain-to-Source Leakage Current      | —    | —    | 20   | $\mu A$             | $V_{DS} = 60V, V_{GS} = 0V$                          |
|                                 |                                      | —    | —    | 250  |                     | $V_{DS} = 60V, V_{GS} = 0V, T_J = 125^\circ\text{C}$ |
| $I_{GSS}$                       | Gate-to-Source Forward Leakage       | —    | —    | 100  | nA                  | $V_{GS} = 20V$                                       |
|                                 | Gate-to-Source Reverse Leakage       | —    | —    | -100 |                     | $V_{GS} = -20V$                                      |
| $R_G$                           | Internal Gate Resistance             | —    | 2.0  | —    | $\Omega$            |                                                      |

**Dynamic @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

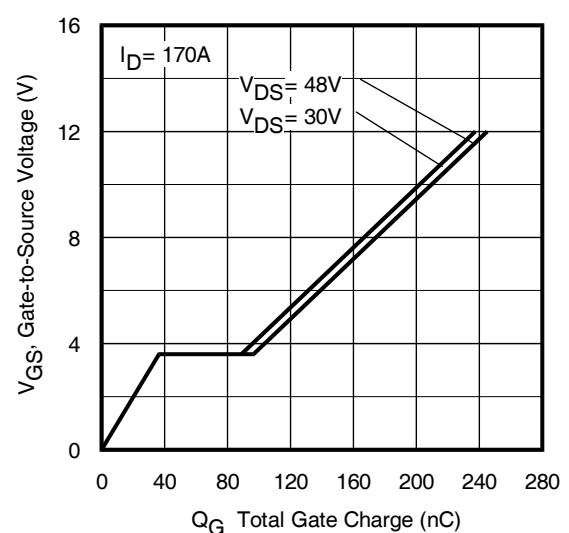
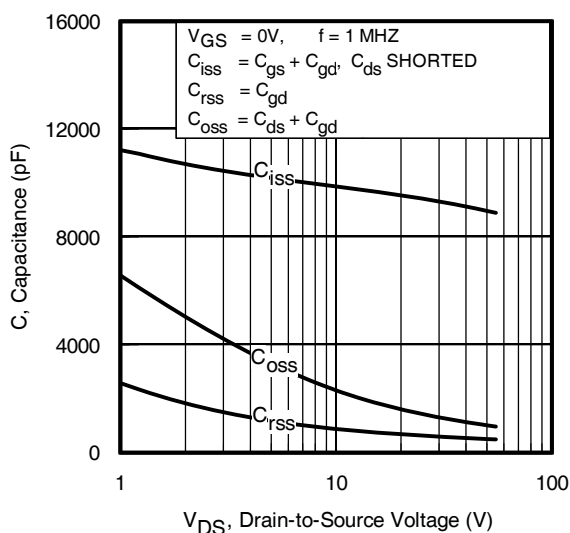
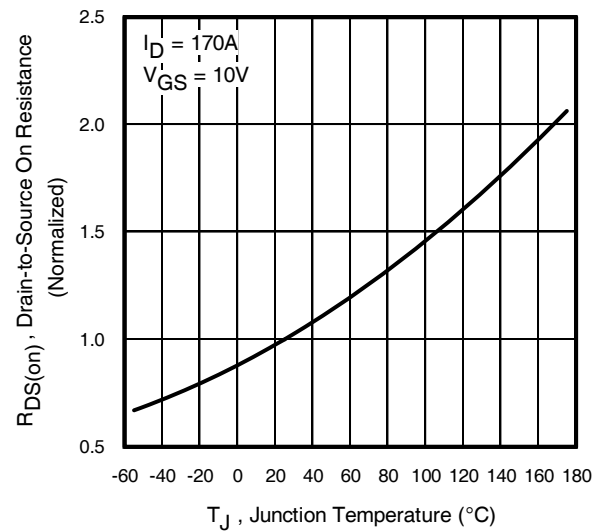
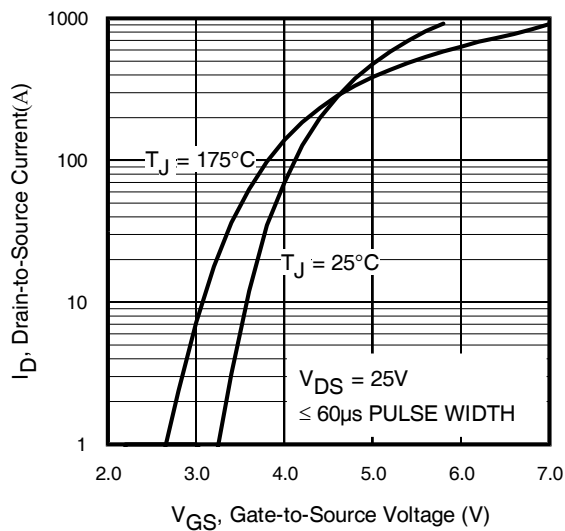
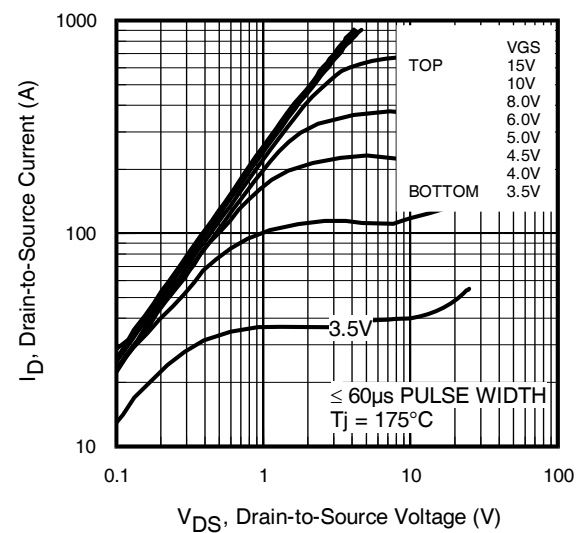
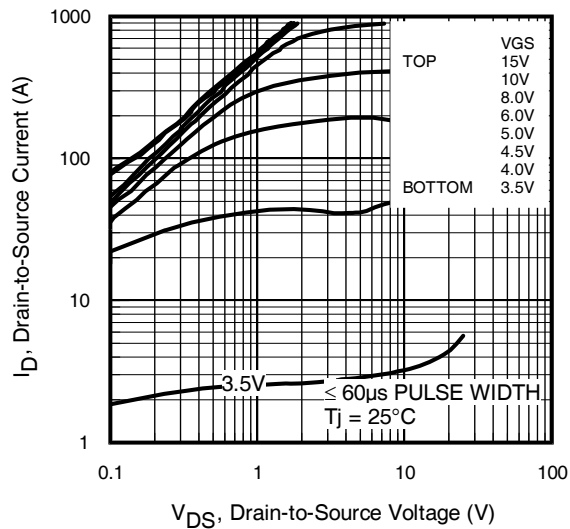
| Symbol                     | Parameter                                     | Min. | Typ. | Max. | Units | Conditions                                           |
|----------------------------|-----------------------------------------------|------|------|------|-------|------------------------------------------------------|
| gfs                        | Forward Transconductance                      | 280  | —    | —    | S     | $V_{DS} = 25V, I_D = 170A$                           |
| $Q_g$                      | Total Gate Charge                             | —    | 200  | 300  | nC    | $I_D = 170A$                                         |
| $Q_{gs}$                   | Gate-to-Source Charge                         | —    | 37   | —    |       | $V_{DS} = 30V$                                       |
| $Q_{gd}$                   | Gate-to-Drain ("Miller") Charge               | —    | 60   | —    |       | $V_{GS} = 10V$ ⑤                                     |
| $Q_{sync}$                 | Total Gate Charge Sync. ( $Q_g - Q_{gd}$ )    | —    | 140  | —    |       | $I_D = 170A, V_{DS} = 0V, V_{GS} = 10V$              |
| $t_{d(on)}$                | Turn-On Delay Time                            | —    | 16   | —    | ns    | $V_{DD} = 39V$                                       |
| $t_r$                      | Rise Time                                     | —    | 182  | —    |       | $I_D = 170A$                                         |
| $t_{d(off)}$               | Turn-Off Delay Time                           | —    | 118  | —    |       | $R_G = 2.7\Omega$                                    |
| $t_f$                      | Fall Time                                     | —    | 189  | —    |       | $V_{GS} = 10V$ ⑤                                     |
| $C_{iss}$                  | Input Capacitance                             | —    | 8970 | —    | pF    | $V_{GS} = 0V$                                        |
| $C_{oss}$                  | Output Capacitance                            | —    | 1020 | —    |       | $V_{DS} = 50V$                                       |
| $C_{rss}$                  | Reverse Transfer Capacitance                  | —    | 534  | —    |       | $f = 1.0\text{ MHz}$ , See Fig. 5                    |
| $C_{oss\text{ eff. (ER)}}$ | Effective Output Capacitance (Energy Related) | —    | 1480 | —    |       | $V_{GS} = 0V, V_{DS} = 0V$ to $48V$ ⑦<br>See Fig. 11 |
| $C_{oss\text{ eff. (TR)}}$ | Effective Output Capacitance (Time Related)   | —    | 1920 | —    |       | $V_{GS} = 0V, V_{DS} = 0V$ to $48V$ ⑥                |

**Diode Characteristics**

| Symbol    | Parameter                              | Min. | Typ. | Max. | Units | Conditions                                                                                                                                           |
|-----------|----------------------------------------|------|------|------|-------|------------------------------------------------------------------------------------------------------------------------------------------------------|
| $I_S$     | Continuous Source Current (Body Diode) | —    | —    | 257① | A     | MOSFET symbol showing the integral reverse p-n junction diode.  |
| $I_{SM}$  | Pulsed Source Current (Body Diode) ②   | —    | —    | 1028 |       |                                                                                                                                                      |
| $V_{SD}$  | Diode Forward Voltage                  | —    | —    | 1.3  | V     | $T_J = 25^\circ\text{C}, I_S = 170A, V_{GS} = 0V$ ④                                                                                                  |
| $t_{rr}$  | Reverse Recovery Time                  | —    | 44   | —    | ns    | $T_J = 25^\circ\text{C}$                                                                                                                             |
|           |                                        | —    | 48   | —    |       | $T_J = 125^\circ\text{C}$                                                                                                                            |
| $Q_{rr}$  | Reverse Recovery Charge                | —    | 63   | —    | nC    | $T_J = 25^\circ\text{C}$                                                                                                                             |
|           |                                        | —    | 77   | —    |       | $T_J = 125^\circ\text{C}$                                                                                                                            |
| $I_{RRM}$ | Reverse Recovery Current               | —    | 2.4  | —    | A     | $T_J = 25^\circ\text{C}$<br>$V_R = 51V, I_F = 170A, di/dt = 100A/\mu s$ ⑤                                                                            |

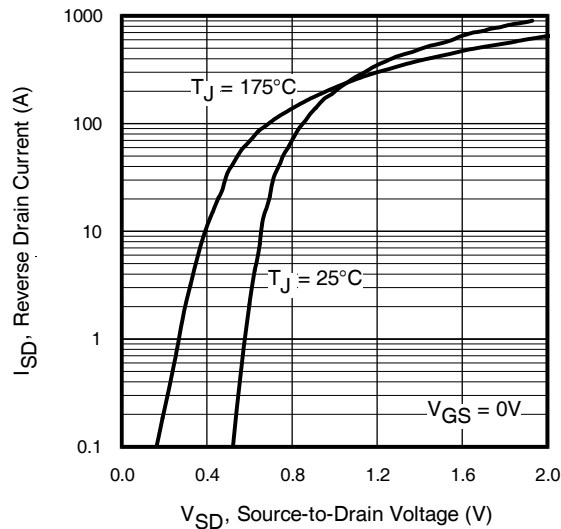
**Notes:**

- ① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 195A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. (Refer to AN-1140)
- ② Repetitive rating; pulse width limited by max. Junction temperature.
- ③ Limited by  $T_{Jmax}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.022mH$ ,  $R_G = 50\Omega$ ,  $I_{AS} = 170A, V_{GS} = 10V$ . Part not Recommended for use above this value.
- ④  $I_{SD} \leq 170A, di/dt \leq 1360A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$ .
- ⑤ Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .
- ⑥  $C_{oss\text{ eff. (TR)}}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑦  $C_{oss\text{ eff. (ER)}}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑧  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .
- \* All spec data and curves based on (TO-220 Pak -IRFP3006PbF) Datasheet.

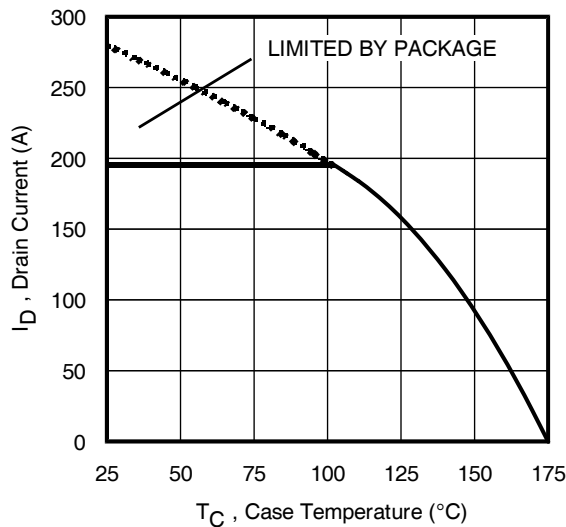


**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage

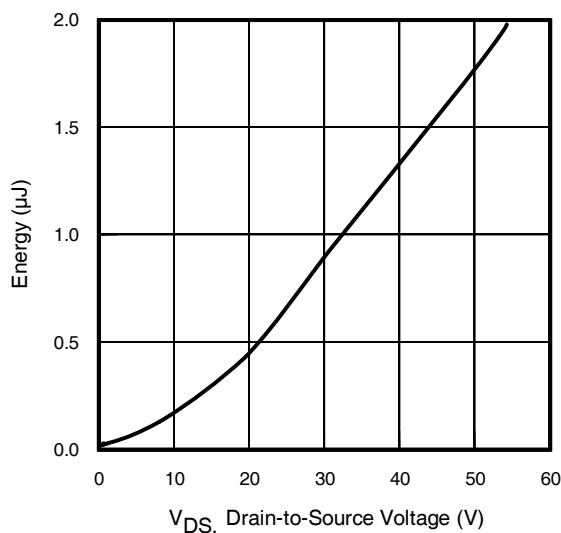
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



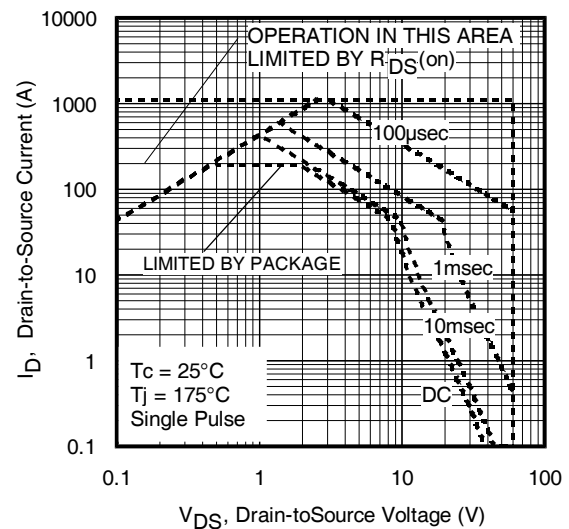
**Fig 7.** Typical Source-to-Drain Diode Forward Voltage



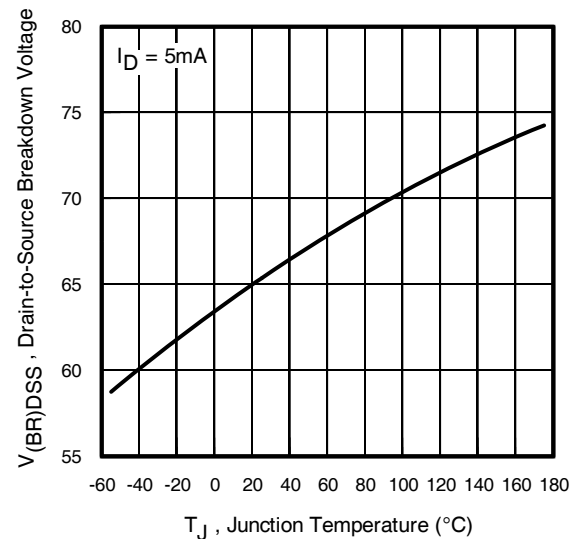
**Fig 9.** Maximum Drain Current vs. Case Temperature



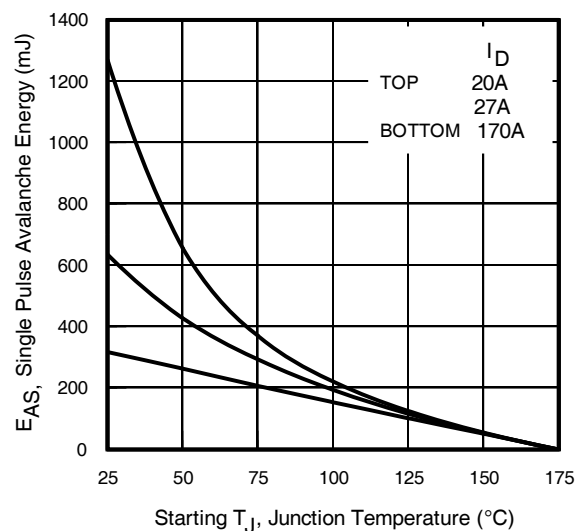
**Fig 11.** Typical  $C_{oss}$  Stored Energy



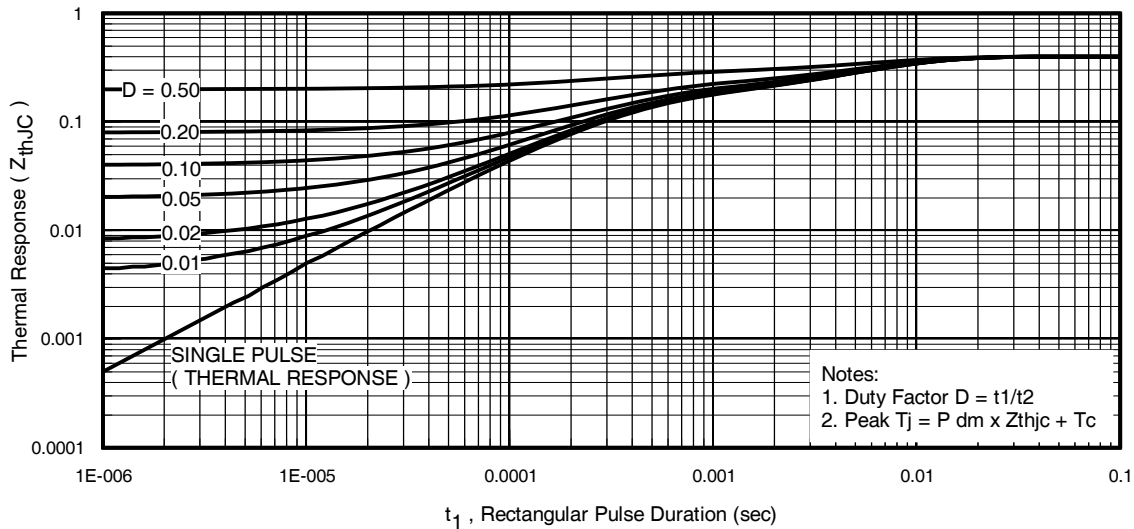
**Fig 8.** Maximum Safe Operating Area



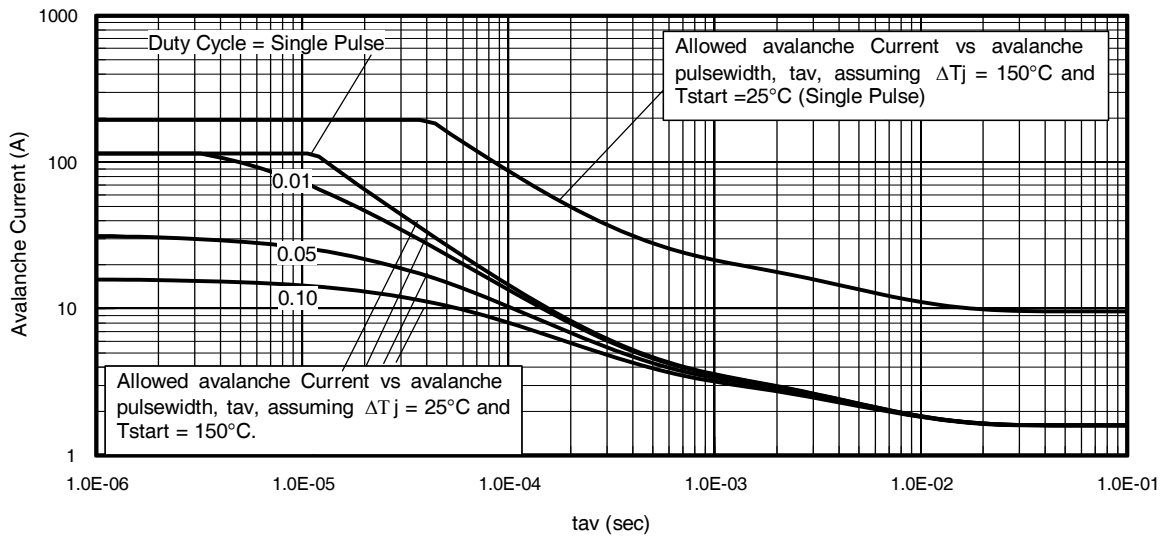
**Fig 10.** Drain-to-Source Breakdown Voltage



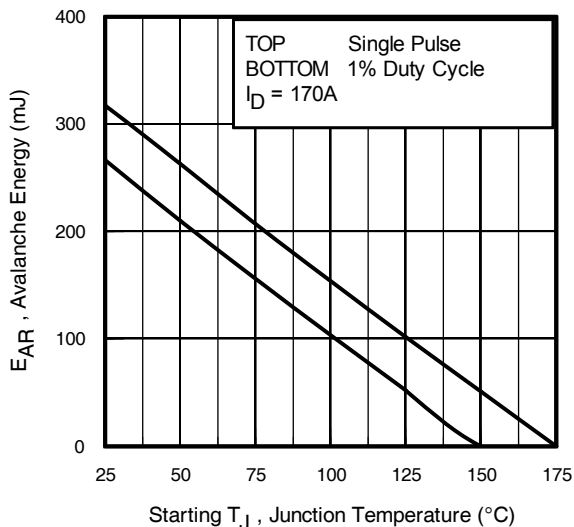
**Fig 12.** Maximum Avalanche Energy vs. Drain Current



**Fig 13.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



**Fig 14.** Typical Avalanche Current vs. Pulsewidth



**Fig 15.** Maximum Avalanche Energy vs. Temperature

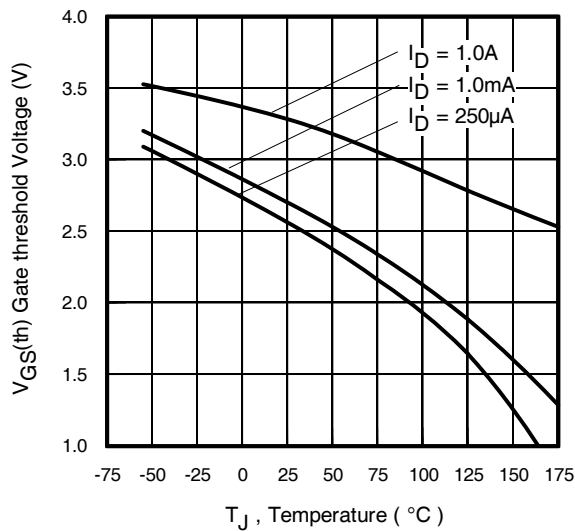
**Notes on Repetitive Avalanche Curves , Figures 14, 15:**  
(For further info, see AN-1005 at [www.irf.com](http://www.irf.com))

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of Tjmax. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as Tjmax is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed Tjmax (assumed as 25°C in Figure 14, 15).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see Figures 13)

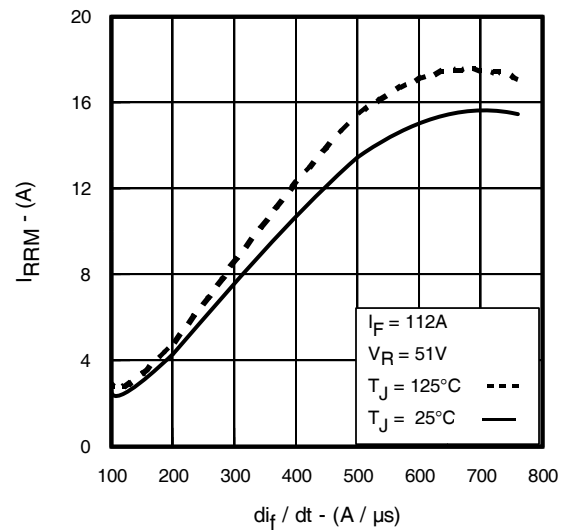
$$P_{D(ave)} = \frac{1}{2} (1.3 \cdot BV \cdot I_{av}) = \frac{\Delta T}{Z_{thJC}}$$

$$I_{av} = \frac{2\Delta T}{[1.3 \cdot BV \cdot Z_{thJC}]}$$

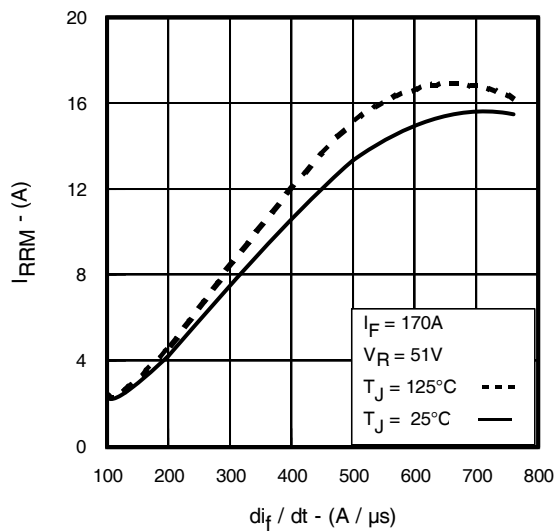
$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$



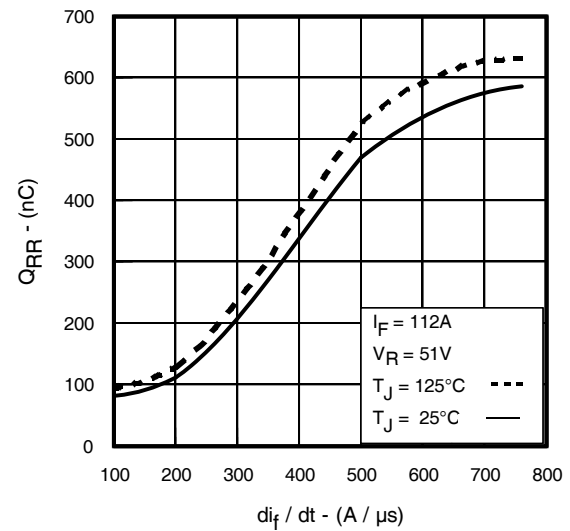
**Fig. 16** Threshold Voltage vs. Temperature



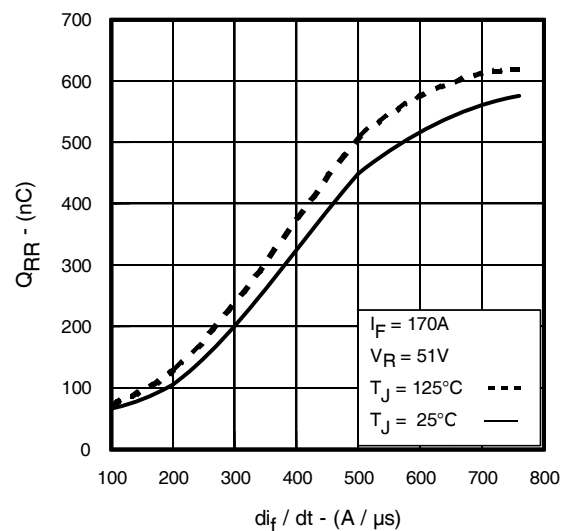
**Fig. 17** Typical Recovery Current vs.  $di_f/dt$



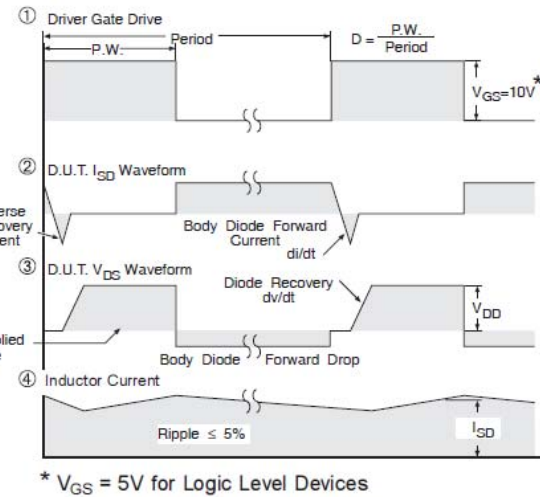
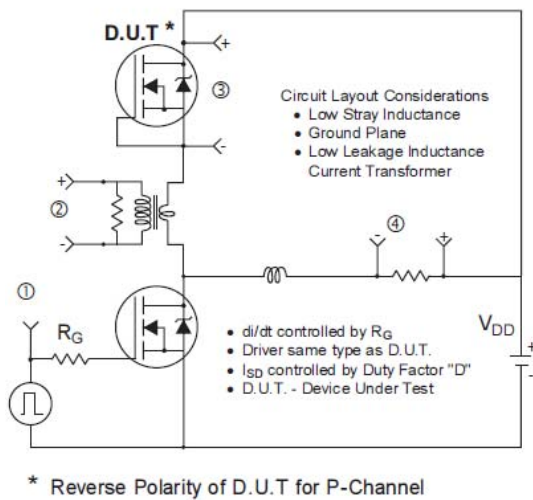
**Fig 18.** Typical Recovery Current vs.  $di_f/dt$



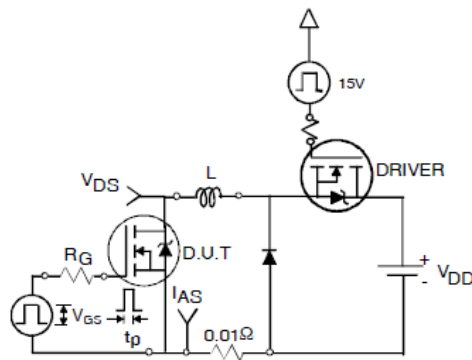
**Fig 19.** Typical Stored Charge vs.  $di_f/dt$



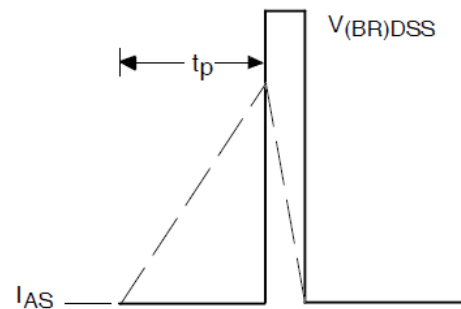
**Fig 20.** Typical Stored Charge vs.  $di_f/dt$



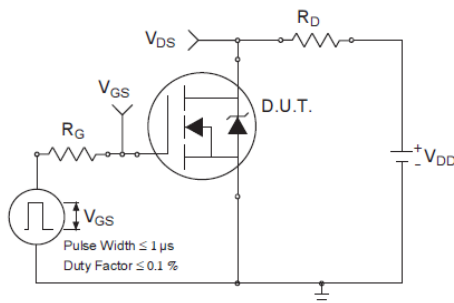
**Fig 21.** Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs



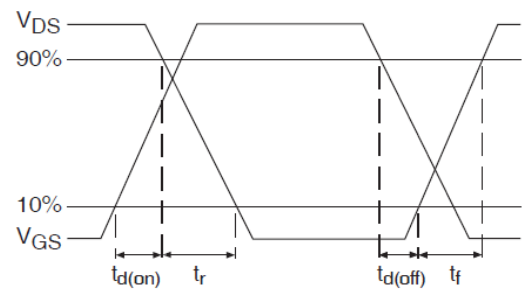
**Fig 22a.** Unclamped Inductive Test Circuit



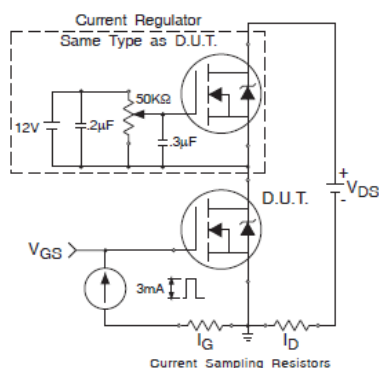
**Fig 22b.** Unclamped Inductive Waveforms



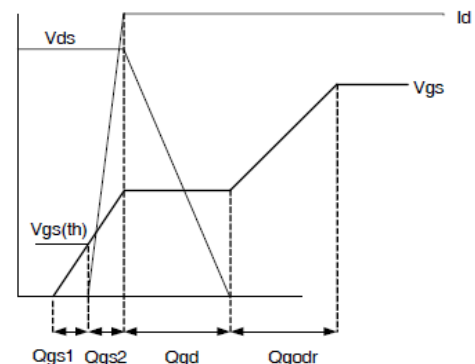
**Fig 23a.** Switching Time Test Circuit



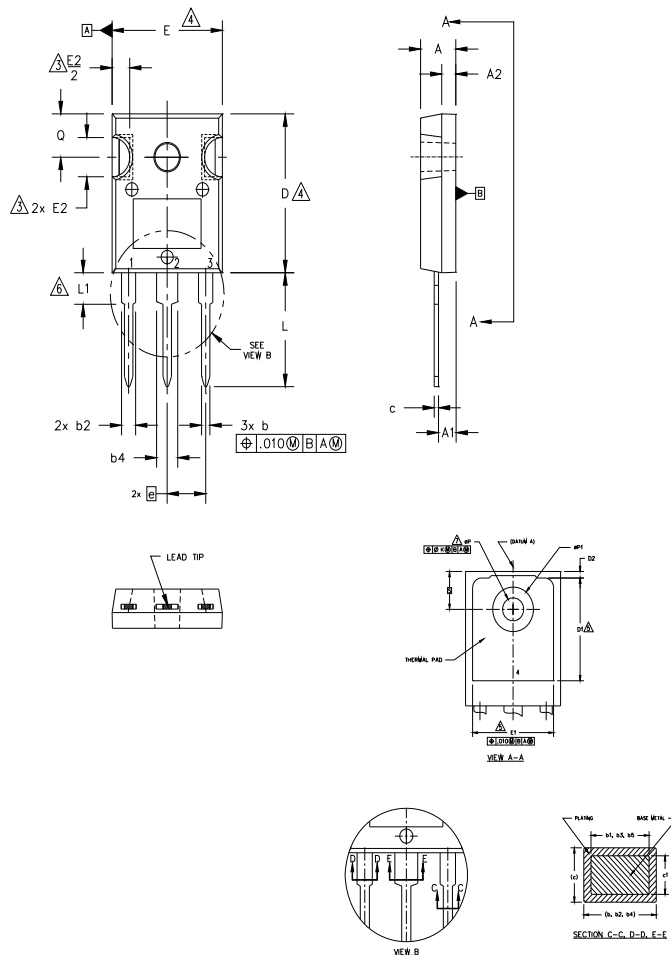
**Fig 23b.** Switching Time Waveforms



**Fig 24a.** Gate Charge Test Circuit



**Fig 24b.** Gate Charge Waveform

**TO-247AC Package Outline (Dimensions are shown in millimeters (inches))**

**NOTES:**

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

| SYMBOL | DIMENSIONS |      |             |       | NOTES |
|--------|------------|------|-------------|-------|-------|
|        | INCHES     |      | MILLIMETERS |       |       |
|        | MIN.       | MAX. | MIN.        | MAX.  |       |
| A      | .183       | .209 | 4.65        | 5.31  |       |
| A1     | .087       | .102 | 2.21        | 2.59  |       |
| A2     | .059       | .098 | 1.50        | 2.49  |       |
| b      | .039       | .055 | 0.99        | 1.40  |       |
| b1     | .039       | .053 | 0.99        | 1.35  |       |
| b2     | .065       | .094 | 1.65        | 2.39  |       |
| b3     | .065       | .092 | 1.65        | 2.34  |       |
| b4     | .102       | .135 | 2.59        | 3.43  |       |
| b5     | .102       | .133 | 2.59        | 3.38  |       |
| c      | .015       | .035 | 0.38        | 0.89  |       |
| c1     | .015       | .033 | 0.38        | 0.84  |       |
| D      | .776       | .815 | 19.71       | 20.70 | 4     |
| D1     | .515       | —    | 13.08       | —     | 5     |
| D2     | .020       | .053 | 0.51        | 1.35  |       |
| E      | .602       | .625 | 15.29       | 15.87 | 4     |
| E1     | .530       | —    | 13.46       | —     |       |
| E2     | .178       | .216 | 4.52        | 5.49  |       |
| e      | .215 BSC   |      | 5.46 BSC    |       |       |
| Øk     | .010       |      | 0.25        |       |       |
| L      | .559       | .634 | 14.20       | 16.10 |       |
| L1     | .146       | .169 | 3.71        | 4.29  |       |
| ØP     | .140       | .144 | 3.56        | 3.66  |       |
| ØP1    | —          | .291 | —           | 7.39  |       |
| Q      | .209       | .224 | 5.31        | 5.69  |       |
| S      | .217 BSC   |      | 5.51 BSC    |       |       |

**LEAD ASSIGNMENTS**
**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

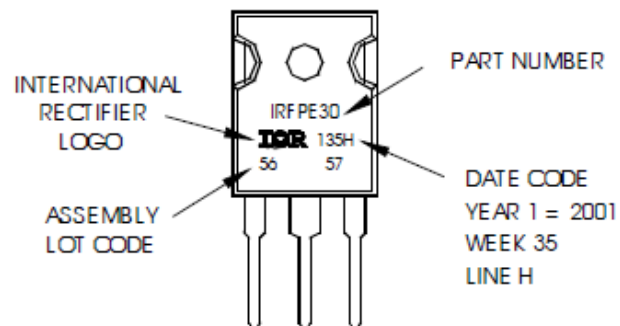
**DIODES**

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

**TO-247AC Part Marking Information**

EXAMPLE: THIS IS AN IRFPE30  
WITH ASSEMBLY  
LOT CODE 5657  
ASSEMBLED ON WW 35, 2001  
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position  
indicates "Lead-Free"



TO-247AC package is not recommended for Surface Mount Application.

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Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

**Qualification information<sup>†</sup>**

|                            |                                                  |     |
|----------------------------|--------------------------------------------------|-----|
| Qualification level        | Industrial<br>(per JEDEC JESD47F ) <sup>††</sup> |     |
| Moisture Sensitivity Level | TO-247AC                                         | N/A |
| RoHS compliant             | Yes                                              |     |

† Qualification standards can be found at International Rectifier's web site <http://www.irf.com/product-info/reliability>

†† Applicable version of JEDEC standard at the time of product release.

International  
 Rectifier

**IR WORLD HEADQUARTERS:** 101N Sepulveda Blvd, El Segundo, California 90245, USA

To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>

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